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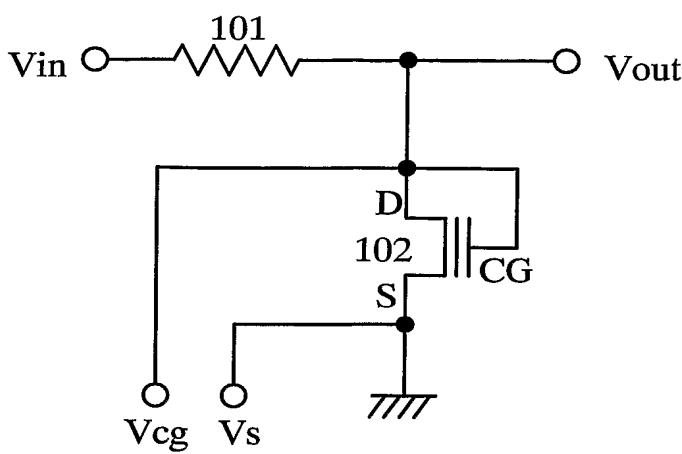
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(54) Title: LIMITER AND SEMICONDUCTOR DEVICE USING THE SAME



(57) Abstract: The limiter of the invention uses as a diode a stacked gate thin film transistor (TFT) including a floating gate. When the TFT including a floating gate is used, the threshold voltage V_{th} may be corrected by controlling the amount of charge accumulated in the floating gate even in the case where there are variations in the threshold voltages V_{th} of the TFT.